

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-4. (Canceled).

5. (Currently Amended) A method for evaluating crystal defects of a silicon wafer comprising:

etching a surface of the silicon wafer by immersing the wafer in an etching solution; and

observing etch pits formed on the etched surface of the wafer,  
wherein the silicon wafer of which crystal defects are evaluated has low  
electrical resistivity of 1  $\Omega\text{-cm}$  or less, and the etching solution is a mixture of hydrofluoric acid, nitric acid, acetic acid and water further including iodine or iodide, ~~in which the etching solution satisfies at least one of (i) a volume ratio of nitric acid in the etching solution is the largest among volume ratios of hydrofluoric acid, nitric acid, acetic acid and water~~ ~~hydrofluoric acid : nitric acid : acetic acid : water is 1 : 13-17 : 4-8 : 4-8 and/or (ii) includes iodine or iodide in a range from 0.01 g to 0.09 g per 1 liter of total liquid volume of the etching solution~~, and the etching solution is adjusted to have an etching rate of 100 nm/min or less for the silicon wafer.

6. (Canceled)

7. (Canceled)

8. (Canceled)

9. (Previously Presented) The method for evaluating crystal defects of a silicon wafer according to Claim 5, wherein a removal amount of the surface of the silicon wafer by etching is 50 nm or more.

10-12. (Canceled)